

HAT1044M

Silicon P Channel Power MOS FET
Power Switching

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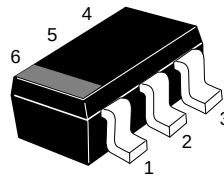
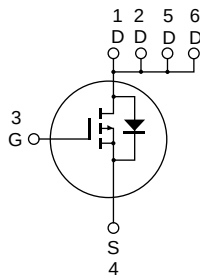
ADE-208-753C(Z)
Preliminary
4th. Edition
December 1998

Features

- Low on-resistance
- Low drive current
- High density mounting
- 4.5V gate drive device can be driven from 5V source

Outline

TSOP-6



4 Source
3 Gate
1, 2, 5, 6 Drain

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-30	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D^{*2}	-4.5	A
Drain peak current	$I_{D(pulse)}^{*1}$	-18	A
Body-drain diode reverse drain current	I_{DR}^{*2}	-4.5	A
Channel dissipation	$Pch_{(pulse)}^{*2}$	2.0	W
	$Pch_{(continuous)}^{*3}$	1.05	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$
2. When using the alumina ceramic board (50 x 50 x 0.7 mm), $PW \leq 5s$, $Ta = 25^\circ C$
3. When using the alumina ceramic board (50 x 50 x 0.7 mm), $Ta = 25^\circ C$

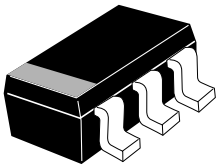
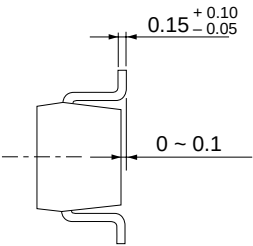
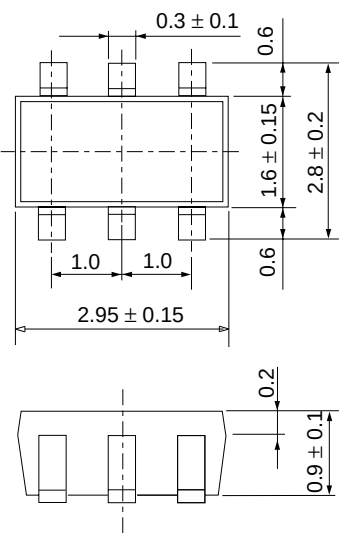
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = 10mA$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20V$, $V_{DS} = 0$
Zero gate voltege drain current	I_{DSS}	—	—	-1	μA	$V_{DS} = -30V$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.5	V	$V_{DS} = -10V$, $I_D = -1mA$
Static drain to source on state resistance	$R_{DS(on)}$	—	50	60	m Ω	$I_D = -3A$, $V_{GS} = -10V^{*1}$
	$R_{DS(on)}$	—	80	105	m Ω	$I_D = -3A$, $V_{GS} = -4.5V^{*1}$
Forward transfer admittance	$ y_{fs} $	3	5.5	—	S	$I_D = -3A$, $V_{DS} = -10V^{*1}$
Input capacitance	Ciss	—	600	—	pF	$V_{DS} = -10V$
Output capacitance	Coss	—	220	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	150	—	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	12	—	ns	$V_{GS} = -10V$, $I_D = -3A$
Rise time	t_r	—	85	—	ns	$R_L = 3.3\Omega$
Turn-off delay time	$t_{d(off)}$	—	55	—	ns	
Fall time	t_f	—	55	—	ns	
Body–drain diode forward voltage	V_{DF}	—	-0.95	—	V	IF = -4.5A, $V_{GS} = 0^{*1}$
Body–drain diode reverse recovery time	t_{rr}	—	50	—	ns	IF = -4.5A, $V_{GS} = 0$ diF/ dt = -20A/ μs

Note: 1. Pulse test

Package Dimensions

Unit: mm



Hitachi Code	TSOP-6
EIAJ	-
JEDEC	-

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